



VOIDLESS HERMETICALLY SEALED SWITCHING DIODES

Qualified per MIL-PRF-19500/578

Qualified Levels:
JAN, JANTX,
JANTXV and JANS

DESCRIPTION

This popular surface mount equivalent JEDEC registered switching/signal diodes are military qualified and available with internal metallurgical bonded construction. These small low capacitance diodes with very fast switching speeds are hermetically sealed and bonded into a "D-5D" package. They may be used in a variety of fast switching applications including computers and peripheral equipment such as magnetic cores, thin-film memories, plated-wire memories, as well as decoding or encoding applications, etc. Microsemi also offers a variety of other switching/signal diodes.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered surface mount equivalents of 1N6638, 1N6642, and 1N6643.
- Ultra fast recovery time.
- Very low capacitance.
- Metallurgically bonded.
- Non-cavity glass package.
- JAN, JANTX, JANTXV and JANS qualifications are available per MIL-PRF-19500/578.
- Replacements for 1N4148UR, 1N4148UR-1, 1N4150UR-1, and 1N914UR.
- RoHS compliant devices available (commercial grade only).

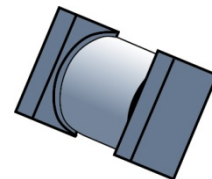
APPLICATIONS / BENEFITS

- Small size for high density mounting (see package illustration).
- Ideal for:
 - High frequency data lines
 - RS-232 & RS-422 Interface Networks
 - Ethernet: 10 Base T
 - Switching core drivers
 - LAN
 - Computers

MAXIMUM RATINGS @ $T_A = +25^\circ\text{C}$ unless otherwise noted.

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temp	T_J and T_{STG}	-65 to +175	$^\circ\text{C}$
Thermal Resistance Junction-to-End Cap	$R_{\theta JEC}$	40	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	250	$^\circ\text{C/W}$
Peak Forward Surge Current @ $T_A = +25^\circ\text{C}$ (Test pulse = 8.3 ms, half-sine wave.)	I_{FSM}	2.5	A
Average Rectified Forward Current @ $T_A = +75^\circ\text{C}$ (Derate at 4.6 mA/ $^\circ\text{C}$ Above $T_{EC} = +110^\circ\text{C}$)	I_O	300	mA
Breakdown Voltage:	V_{BR}	1N6638US 1N6642US 1N6643US	V
		150	
		100	
		75	
Working Peak Reverse Voltage:	V_{RWM}	1N6638US 1N6642US 1N6643US	V
		125	
		75	
		50	

NOTES: 1. $T_A = +75^\circ\text{C}$ on printed circuit board (PCB), PCB = FR4 - .0625 inch (1.59 mm) 1-layer 1-Oz Cu, horizontal, in still air; pads for US = .061 inch (1.55 mm) x .105 inch (2.67 mm); $R_{\theta JA}$ with a defined PCB thermal resistance condition included, is measured at $I_O = 300$ mA.



"D" SQ-MELF (D-5D) Package

Also available in:

"D" Package

(axial-leaded)



[1N6638 42 43](#)

MSC – Lawrence

6 Lake Street,
Lawrence, MA 01841
1-800-446-1158
Tel: (978) 620-2600
Fax: (978) 689-0803

MSC – Ireland

Gort Road Business Park,
Ennis, Co. Clare, Ireland
Tel: +353 (0) 65 6840044
Fax: +353 (0) 65 6822298

Website:

www.microsemi.com

MECHANICAL and PACKAGING

- CASE: Voidless hermetically sealed hard glass.
- TERMINALS: Tin-Lead plate with >3% Lead. Solder dip is available upon request.
- MARKING: Body painted and alpha numeric.
- POLARITY: Cathode indicated by band.
- Tape & Reel option: Standard per EIA-481-1-A with 12 mm tape. Consult factory for quantities.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE

JAN 1N6638 US (e3)

Reliability Level

JAN = JAN Level
JANTX = JANTX Level
JANTXV = JANTXV Level
JANS = JANS Level
Blank = commercial

JEDEC type number

See [Electrical Characteristics](#) table

RoHS Compliance

e3 = RoHS compliant (available on commercial grade only)
Blank = non-RoHS compliant

Surface Mount Package
SYMBOLS & DEFINITIONS

Symbol	Definition
V_{BR}	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.
V_{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range.
V_F	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current.
I_R	Maximum Reverse Current: The maximum reverse (leakage) current that will flow at the specified voltage and temperature.
C	Capacitance: The capacitance in pF at a frequency of 1 MHz and specified voltage.
t_{rr}	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified recovery decay point after a peak reverse current is reached.

ELECTRICAL CHARACTERISTICS @ 25°C unless otherwise noted.

TYPE NUMBER	MAXIMUM FORWARD VOLTAGE V_F @ I_F		MAXIMUM DC REVERSE CURRENT				REVERSE RECOVERY TIME t_{rr} (Note 1)	MAXIMUM FORWARD RECOVERY VOLTAGE AND TIME $I_F=200mA, t_r=1ns$		MAXIMUM JUNCTION CAPACITANCE $f = 1 \text{ MHz}$ $V_{sig} = 50 \text{ mV}$ (p-p)	
			I_{R1}	I_{R2}	I_{R3}	I_{R4}					
	$V @ \text{mA}$	$V @ \text{mA}$	$V_R=20 \text{ V}$	$V_R=V_{RWM}$	$V_R=20 \text{ V}$ $T_A=+150^\circ\text{C}$	$V_R=V_{RWM}$ $T_A=+150^\circ\text{C}$		V_{FRM}	t_{rr}	$V_R=0 \text{ V}$	$V_R=1.5 \text{ V}$
	$V @ \text{mA}$	$V @ \text{mA}$	nA	nA	μA	μA	ns	V	ns	pf	pf
1N6638US	0.8 V @ 10 mA	1.1 V @ 200 mA	35	500	50	100	4.5	5.0	20	2.5	2.0
1N6642US	0.8 V @ 10 mA	1.2 V @ 100 mA	25	500	50	100	5.0	5.0	20	5.0	2.8
1N6643US	0.8 V @ 10 mA	1.2 V @ 100 mA	50	500	75	100	6.0	5.0	20	5.0	2.8

NOTE: 1. Reverse Recovery Time Test Conditions – $I_F=I_R=10 \text{ mA}$, $I_{R(REC)} = 1.0 \text{ mA}$, $C=3 \text{ pF}$, $R_L = 100 \text{ ohms}$.

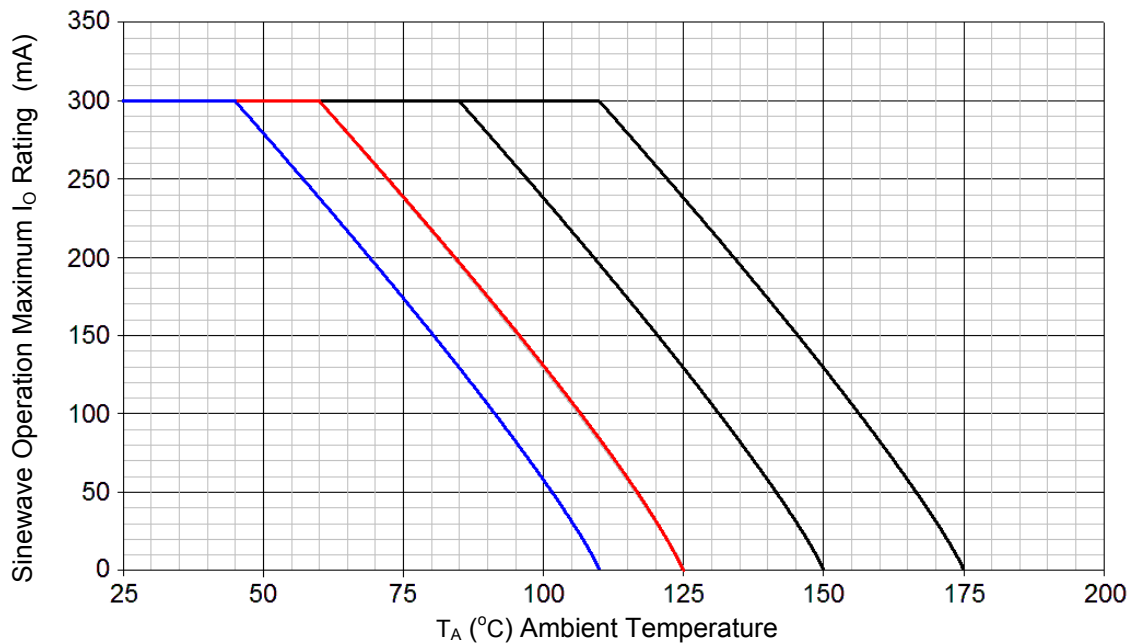
GRAPHS


FIGURE 1
Temperature – Current Derating

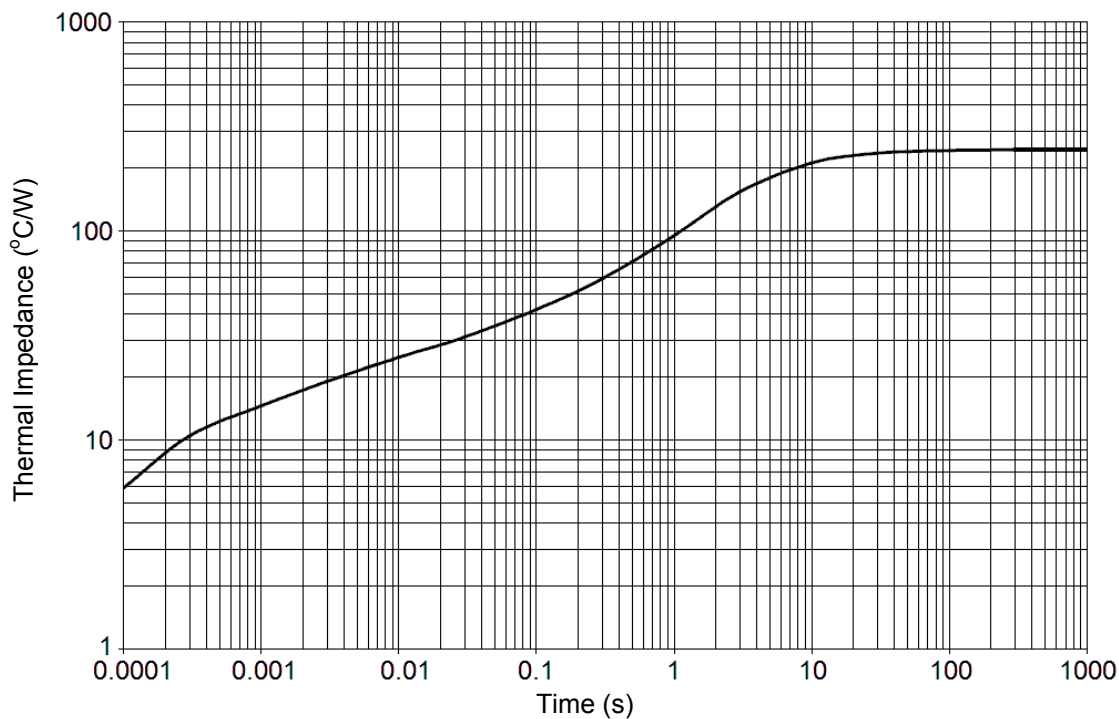


FIGURE 2
Maximum Thermal Impedance at $T_A = 55^\circ\text{C}$

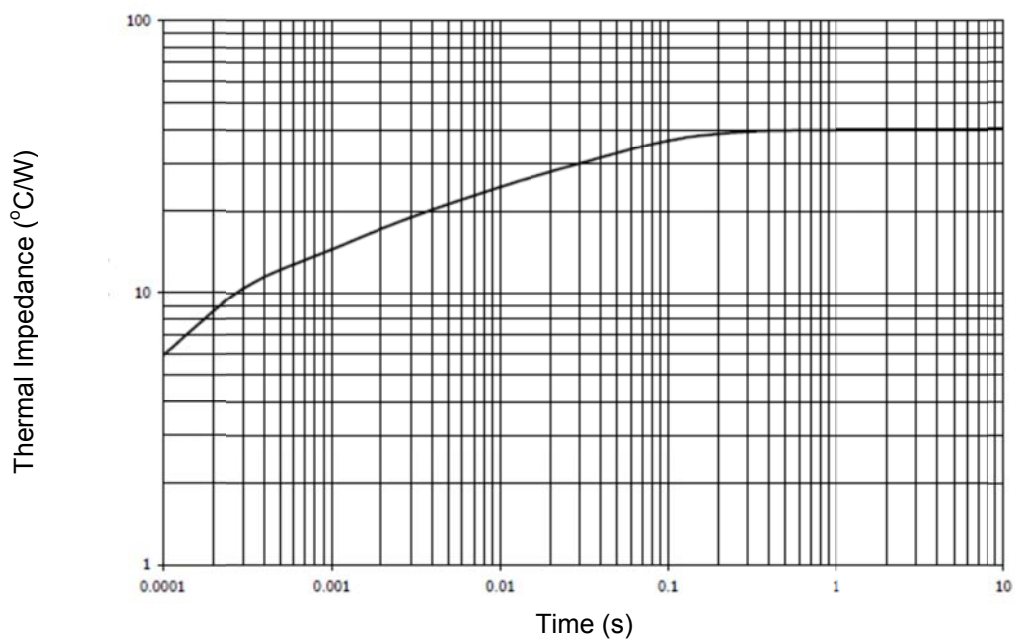
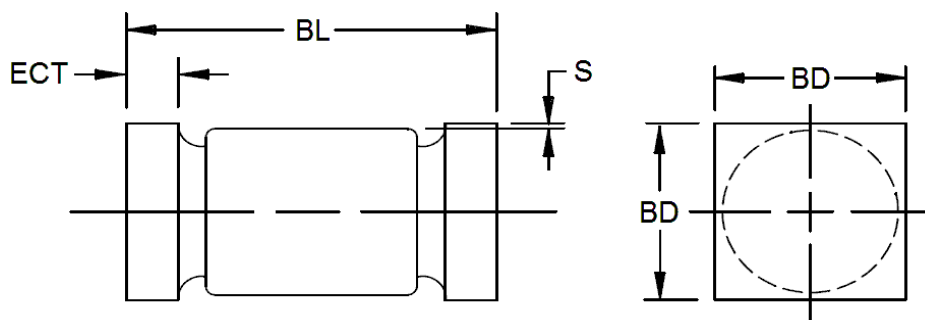
GRAPHS (continued)


FIGURE 3
Maximum Thermal Impedance at $T_{EC} = 25^{\circ}\text{C}$

PACKAGE DIMENSIONS
D-5D


DIM	INCH		MILLIMETERS	
	MIN	MAX	MIN	MAX
BD	0.070	0.085	1.78	2.16
ECT	0.019	0.028	0.48	0.71
BL	0.165	0.195	4.19	4.95
S	0.003 MIN.		0.08 MIN.	

NOTES:

1. Dimensions are in inches. Millimeters are given for general information only.
2. Dimensions are pre-solder dip.
3. U-suffix parts are structurally identical to the US-suffix parts.
4. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.

Данный компонент на территории Российской Федерации

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<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9